



# Derivation of approximately model for CVD graphene growth

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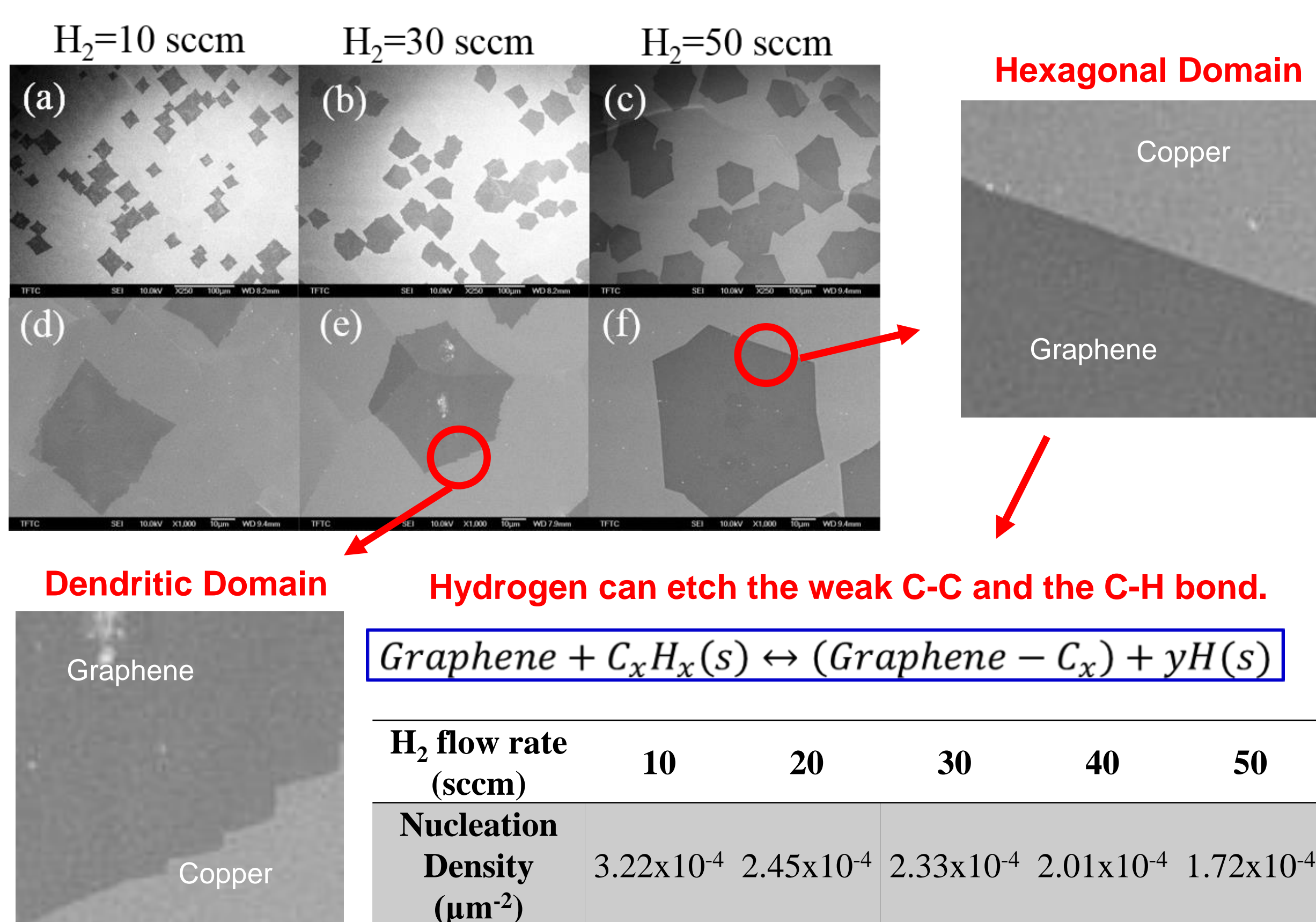
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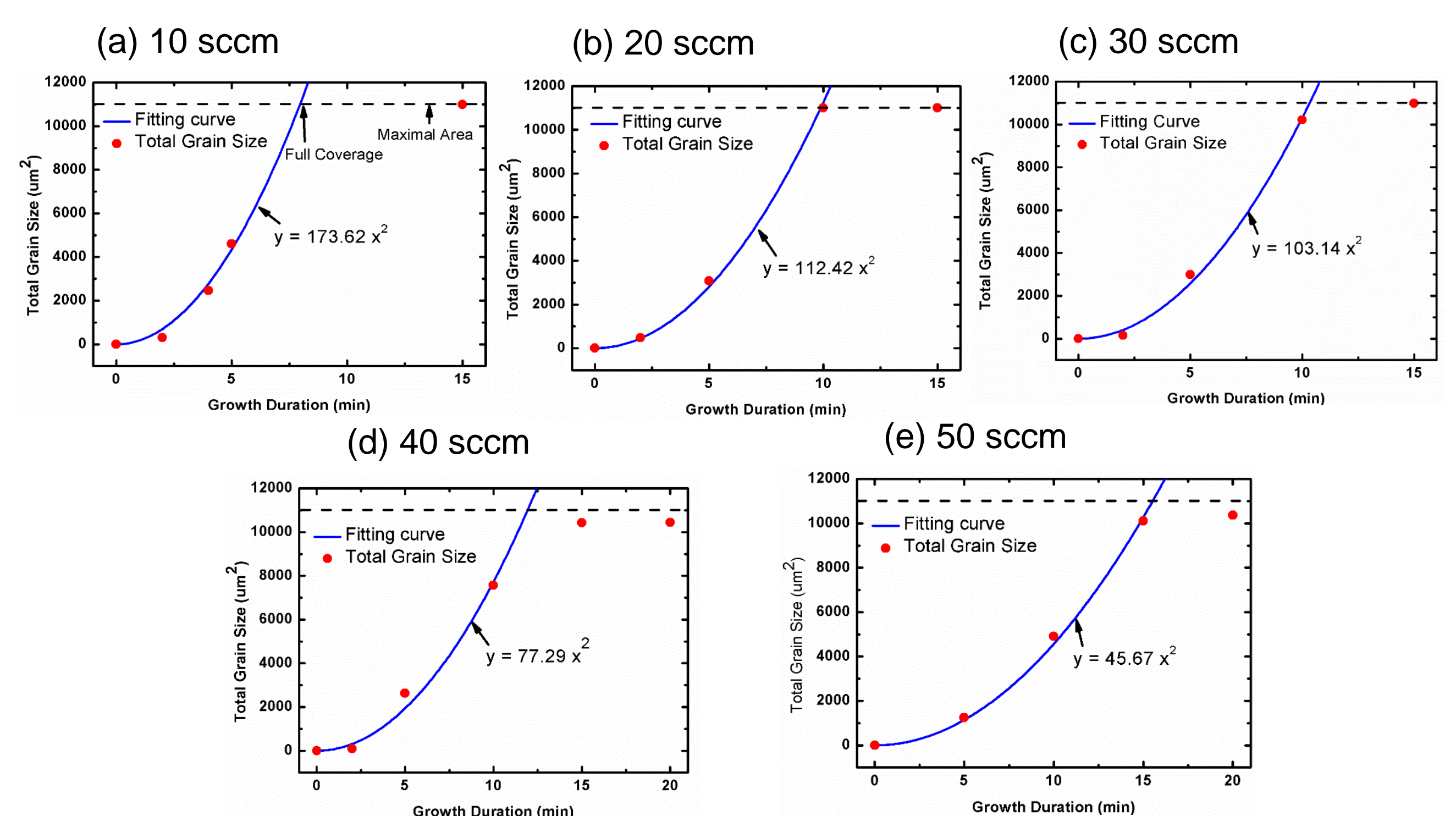
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The aim in this study is controlling the nucleation density of graphene seed, furthermore, pursuing a lower sheet resistance by reducing the quantity of grain boundaries. We developed a simple derivation of approximately model for graphene growth under different hydrogen flow rate, ranging from 10 to 50 sccm. The morphology of graphene edge was become smoother with a high concentration of hydrogen flow rate. The growth parameters, CH<sub>4</sub> and temperature, are 0.5 sccm and 1070°C with ambient chemical vapor deposition (APCVD). The lowest sheet resistance of single layer graphene was 310 Ω/□ and the average transmittance is 97.7 % between 350 -1000 nm wavelengths.

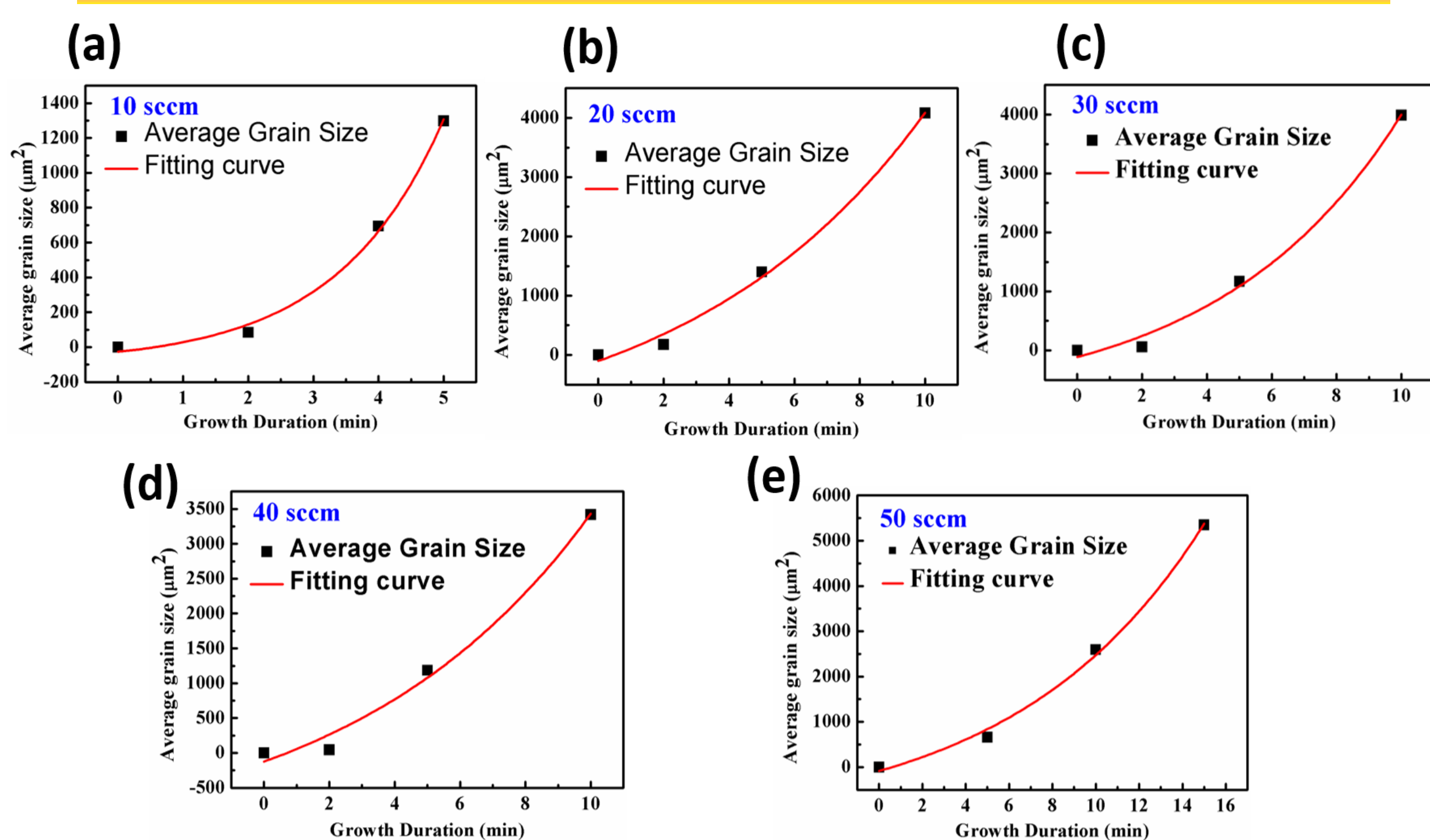
## Coverage Area of Graphene Domains



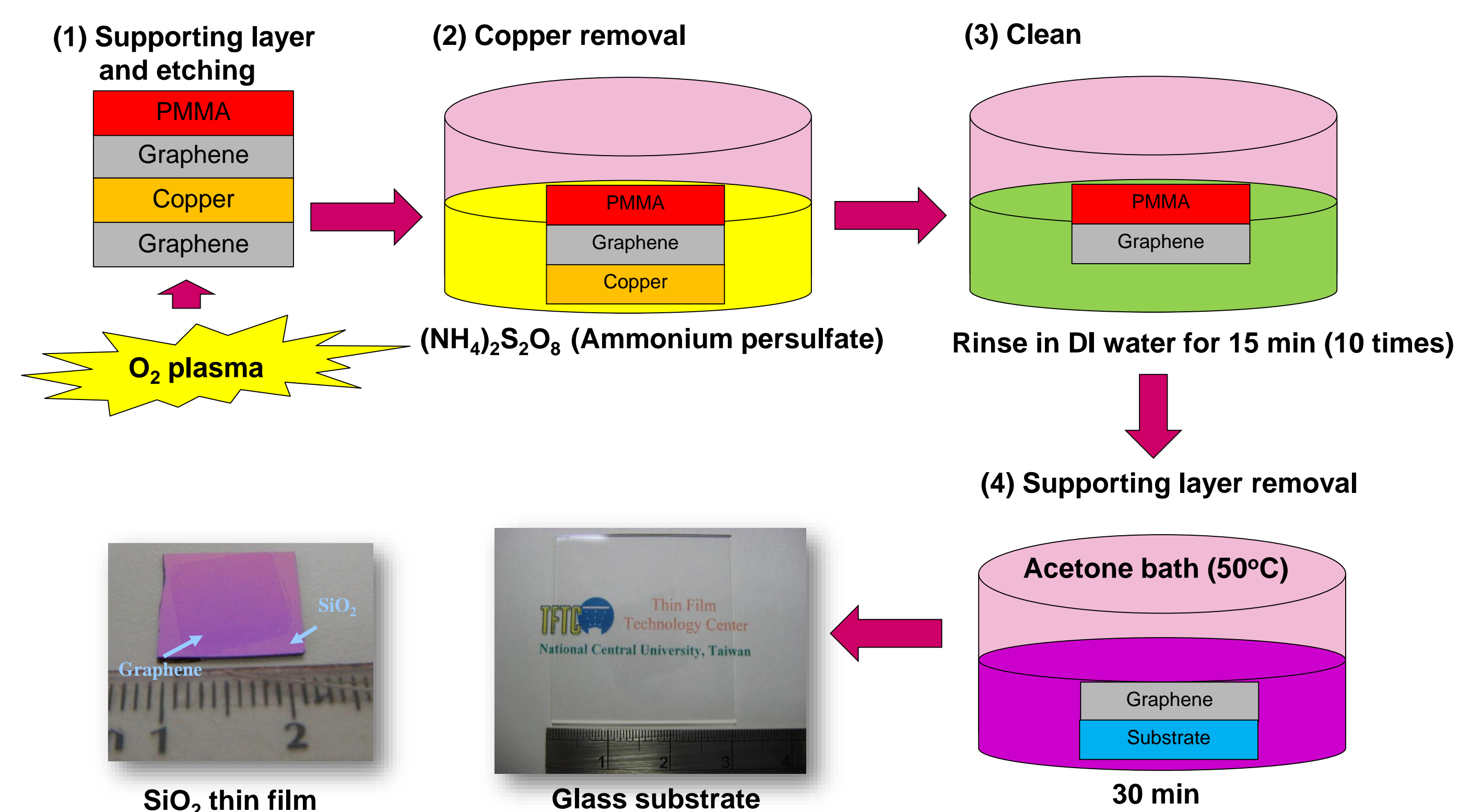
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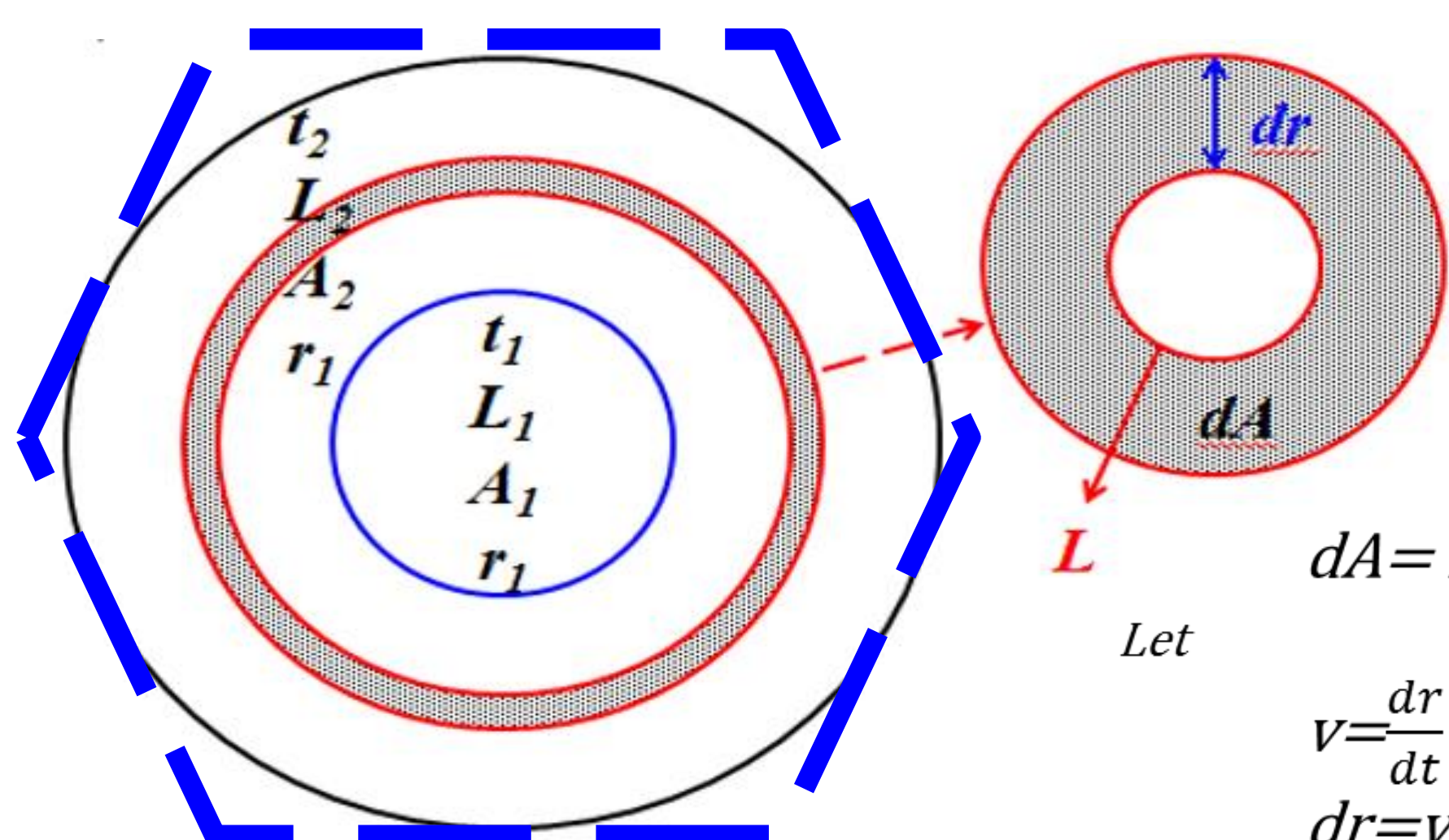
## Carbon Growth Rate



## Transfer Process



## Derivation of the Approximately model



$$dA = Ldr$$

Let

$$v = \frac{dr}{dt}$$

$$dr = vdt$$

And

$$dA = Lvdt$$

$$L = (4\pi A)^{\frac{1}{2}}$$

$$(4\pi A)^{\frac{1}{2}} dA = vdt$$

$$\frac{1}{2\pi} (4\pi A)^{\frac{1}{2}} = vt$$

$$A = \pi(vt)^2$$

$$A = \pi(vt)^2 = \frac{1}{2} \frac{d^2 A}{dt^2} t^2$$

t = growth time  
L = circumference  
A = average area  
r = average radius

The average area is the second-order function of the growth time and growth rate of carbon atoms.

## Summary

